

BROAD AREA LASER

GaAs Semiconductor Laser Diode
Single Emitter Structure



PRELIMINARY SPECIFICATION

BA Laser

EYP-BAL-1064-08000-4020-CMT04-0000**General Product Information**

Product	Application
1064 nm Broad Area Laser	Material Processing
mounted on C-Mount	Medical

**Absolute Maximum Ratings**

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_C	°C	5		40
Forward Current	I_F	A			15
Reverse Voltage	V_R	V			0
Output Power	P_{opt}	W			9

Measurement Conditions / Comments

non condensing

non condensing

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device reliability and may lead to reduced operational life.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_C	°C	15		30
Forward Current	I_F	A			13
Output Power	P_{opt}	W			8

Measurement Conditions / Comments

measured at position A (see drawing on p. 3)

Characteristics at $T_{amb} 25\text{ °C}$ at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_C	nm	1049	1064	1079
Spectral Width (FWHM)	$\Delta\lambda$	nm			6
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.4	
Output Power @ $I_F = 13\text{ A}$	P_{opt}	W	8		
Slope Efficiency	η_d	W / A	0.6	0.7	
Threshold Current	I_{th}	A			2.5

Measurement Conditions / Comments

see images on page 4

total output measured with integrating sphere

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RWE/RWL



BAL



DFB/DBR



TPL/TPA

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Parameter	Symbol	Unit	min	typ	max
Operational Current @ $P_{opt} = 8$ W	I_{op}	A			13
Stripe Width	W_s	μm		200	
Cavity Length	L	μm		4000	
Divergence parallel (FWHM)	$\Theta_{ }$	$^{\circ}$		10	
Divergence perpendicular (FWHM)	Θ_{\perp}	$^{\circ}$		30	
Spectral Mode (longitudinal)				Multi Mode	
Polarization				TE	

Measurement Conditions / Comments

Polarization in perpendicular plane

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RWE/RWL



BAL



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TPL/TPA

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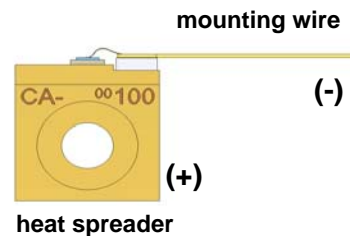
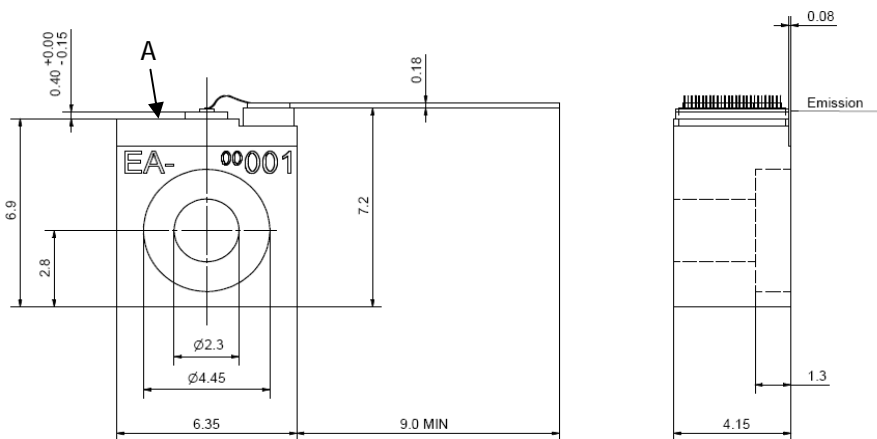
BA Laser

EYP-BAL-1064-08000-4020-CMT04-0000**Package Dimensions**

	Symbol	Unit	min	typ	max
Emission Plane	l	mm	7.05	7.20	7.35
C-Mount Thickness	d	mm		4	

Package Pinout

Cathode (-)	Mounting Wire
Anode (+)	Housing

**Package Drawings**

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Spectrum at Specified Optical Output Power: t.b.d.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

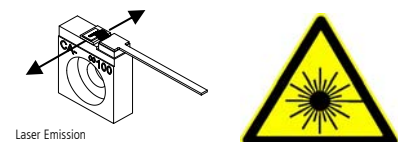
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

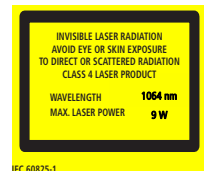
The BAL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



Laser Emission



IEC 60825-1



Complies with 21 CFR 1040.10 and 1040.40



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